

**Silicon PNP Power Transistors****2SA1671****DESCRIPTION**

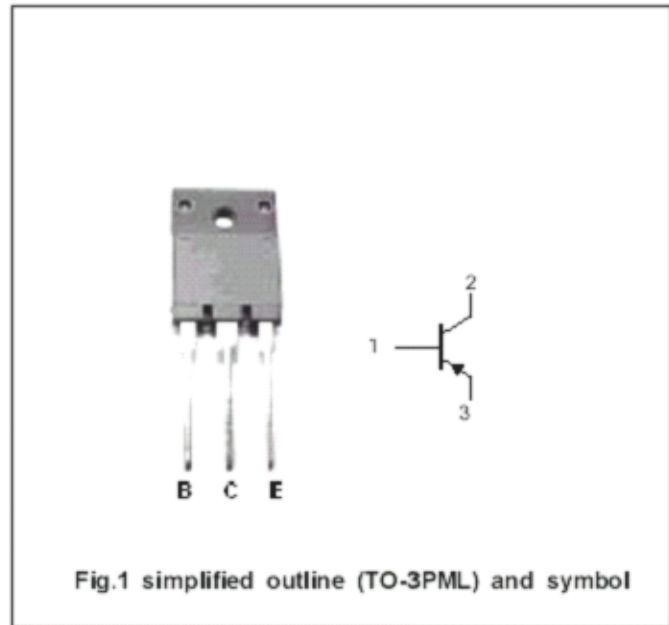
- With TO-3PML package
- Complement to type 2SC4386

APPLICATIONS

- Audio and general purpose

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

**Fig.1 simplified outline (TO-3PML) and symbol****Absolute maximum ratings(Ta=25℃)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-120	V
V_{CEO}	Collector-emitter voltage	Open base	-120	V
V_{EBO}	Emitter-base voltage	Open collector	-6	V
I_C	Collector current		-8	A
I_B	Base current		-3	A
P_C	Collector power dissipation	$T_C=25^{\circ}\text{C}$	75	W
T_j	Junction temperature		150	$^{\circ}\text{C}$
T_{stg}	Storage temperature		-55~150	$^{\circ}\text{C}$



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CHARACTERISTICS

 $T_j=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=-50\text{mA}$; $I_B=0$	-120			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=-1\text{mA}$; $I_C=0$	-6			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-3\text{A}$; $I_B=-0.3\text{A}$			-0.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=-120\text{V}$; $I_E=0$			-10	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=-6\text{V}$; $I_C=0$			-10	μA
h_{FE}	DC current gain	$I_C=-3\text{A}$; $V_{CE}=-4\text{V}$	50		180	
f_T	Transition frequency	$I_C=-0.5\text{A}$; $V_{CE}=-12\text{V}$		20		MHz

◆ h_{FE} classifications

O	P	Y
50-100	70-140	90-180



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PACKAGE OUTLINE

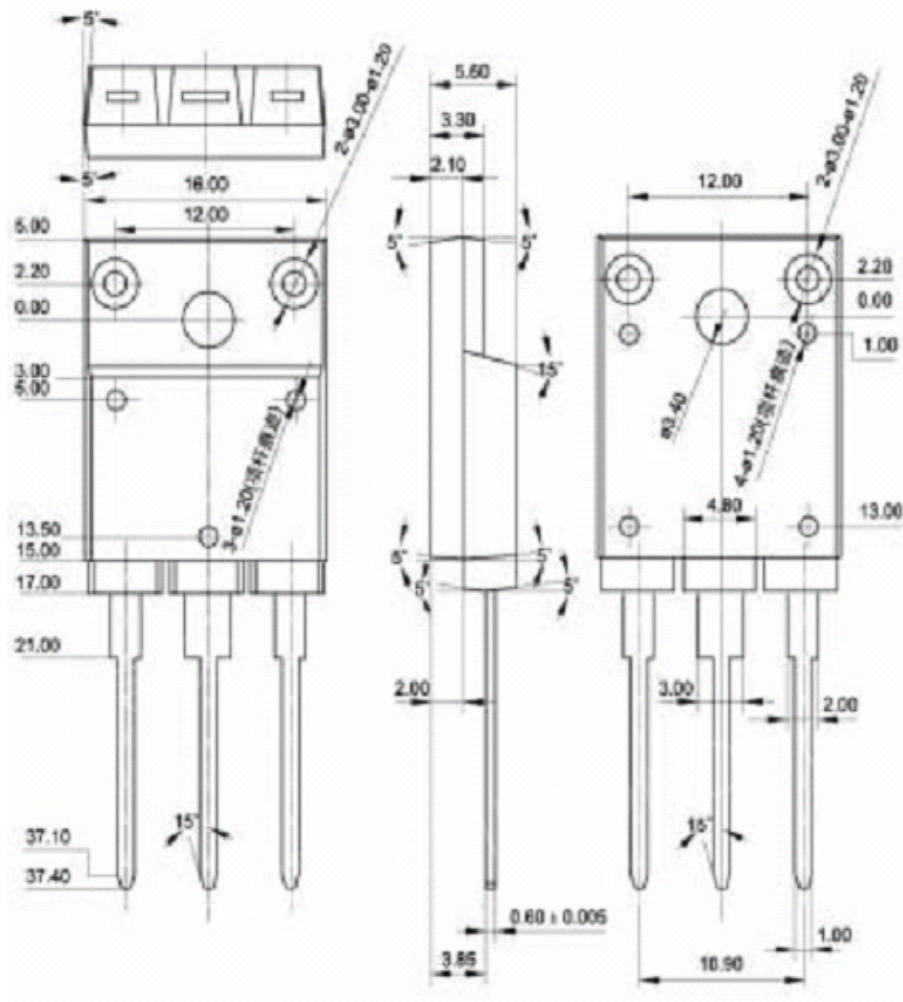


Fig.2 Outline dimensions